

# 200-mA, Low IQ, Low-Noise, Low-Dropout Regulator in Ultra-Small 0.8-mm x 0.8-mm WCSP

#### **FEATURES**

- Very Low Dropout:
  - 105 mV at I<sub>OUT</sub> = 150 mA
  - 145 mV at  $I_{OUT} = 200 \text{ mA}$
- Accuracy: 0.5% Typical
- Low Io: 35 µA
- Available in Fixed-Output Voltages from 0.7 V to 4.8 V
- High PSRR: 70 dB at 1 kHz
- Stable with Effective Capacitance of 0.1 µF
- **Thermal Shutdown and Overcurrent Protection**
- Available in 0.8-mm x 0.8-mm WCSP
- **Available in Two WCSP Height Options:** 
  - YFF: 0.625 mm Max Height
  - YFP: 0.5 mm Max Height

### **APPLICATIONS**

- Wireless Handsets
- **Smart Phones, PDAs**
- **MP3 Players**
- Zigbee™ Networks
- Bluetooth® Devices
- Other Li-Ion Operated Hand-Held Products
- WLAN and Other PC Add-On Cards

YFF, YFP PACKAGES WCSP-4 (TOP VIEW)

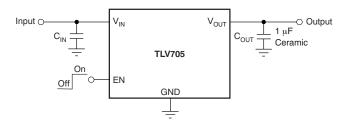


#### DESCRIPTION

The TLV705 series of low-dropout (LDO) linear regulators are low quiescent current devices with excellent line and load transient performance. Designed for power-sensitive applications, a precision bandgap and error amplifier provides typical accuracy of 0.5%. Low output noise, very high power-supply rejection ratio (PSRR), and low dropout voltage make this series of LDOs ideal for a wide selection of battery-operated hand-held equipment. All devices have a thermal shutdown and current limit for safety.

Furthermore, the TLV705 is stable with an effective output capacitance of only 0.1 µF. This feature enables the use of cost-effective capacitors that have higher bias voltage and temperature derating. The devices regulate to the specified accuracy with zero output load. The TLV705P series also provides an active pull-down circuit to quickly discharge output.

The TLV705 and TLV705P series are both available in a 0.8-mm × 0.8-mm WCSP with two height options that are optimal for hand-held applications.



Typical Application Circuit (Fixed-Voltage Versions)

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### **AVAILABLE OPTIONS**(1)

PRODUCT	V <sub>OUT</sub>
TLV705 <b>xx(x)Pyyyz</b>	<b>XX(X)</b> is nominal output voltage. For output voltages with a resolution of 100 mV, two digits are used in the ordering number; otherwise, three digits are used (for example 28 = 2.8 V). <b>P</b> is optional; devices with <b>P</b> have an LDO regulator with an active output discharge. <b>YYY</b> is Package Designator <b>Z</b> is Package Quantity; <b>R</b> is for Reel (3000 pieces), <b>T</b> is for Tape (250 pieces)

<sup>(1)</sup> For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder at www.ti.com.

### ABSOLUTE MAXIMUM RATINGS(1)

Specified at  $T_{\rm J} = -40^{\circ}{\rm C}$  to +125°C, unless otherwise noted. All voltages are with respect to GND.

		VALUE	VALUE	
		MIN	MAX	
	V <sub>IN</sub>	-0.3	6	V
Voltage <sup>(2)</sup>	V <sub>EN</sub>	-0.3	6	V
	V <sub>OUT</sub>	-0.3	6	V
Maximum output current I <sub>OUT</sub>		Internally limit	Internally limited	
Output short-circuit duration		Indefinite		
Continuous total power dissipation	P <sub>DISS</sub>	See Table 2	2	
Tomporoturo	Operating junction, T <sub>J</sub>	<b>-</b> 55	+150	°C
Temperature	Storage, T <sub>stg</sub>	-55	+150	°C
Floatroatatia Disabarga Pating(3)	Human body model (HBM) QSS 009-105 (JESD22-A114A)		2	kV
Electrostatic Discharge Rating (3)	Charged device model (CDM) QSS 009-147 (JESD22-C101B.01)		500	V

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods my affect device reliability.

#### THERMAL INFORMATION

		TLV705	
	THERMAL METRIC <sup>(1)</sup>	YFF, YFP	UNITS
		4 BALLS	
$\theta_{JA}$	Junction-to-ambient thermal resistance	160	
$\theta_{JCtop}$	Junction-to-case (top) thermal resistance	80	
$\theta_{JB}$	Junction-to-board thermal resistance	90	°C/W
ΨЈТ	Junction-to-top characterization parameter	0.5	C/VV
ΨЈВ	Junction-to-board characterization parameter	78	
$\theta_{JCbot}$	Junction-to-case (bottom) thermal resistance	N/A	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

<sup>(2)</sup> All voltages are with respect to network ground terminal.

<sup>(3)</sup> ESD testing is performed according to the respective JESD22 JEDEC standard.



### **ELECTRICAL CHARACTERISTICS**

At  $T_J = -40^{\circ}\text{C}$  to +125°C,  $V_{IN} = V_{OUT~(typ)} + 0.5~V$  or 2 V (whichever is greater),  $I_{OUT} = 10$  mA,  $V_{EN} = 0.9~V$ , and  $C_{OUT} = 1~\mu\text{F}$ , unless otherwise noted. Typical values are at  $T_J = +25^{\circ}\text{C}$ .

			1					
PARAMETER		TES	MIN	TYP	MAX	UNIT		
V <sub>IN</sub>	Input voltage range		2		5.5	V		
V <sub>OUT</sub>	Output voltage range			0.7		4.8	V	
	DC cutout accuracy	-40°C ≤ T <sub>1</sub> ≤ +125°C	0 mA ≤ I <sub>OUT</sub> ≤ 200 mA, V <sub>OUT</sub> ≥ 1 V	-2	±0.5	2	%	
Vo	DC output accuracy	-40 C ≤ IJ ≤ +125 C	$0 \text{ mA} \le I_{OUT} \le 200 \text{ mA}, V_{OUT} < 1 \text{ V}$	-20	±5	20	mV	
$\Delta V_{O}/\Delta V_{IN}$	Line regulation	$V_{OUT(NOM)} + 0.5 V \le V_{IN} \le$	5.5 V		0.05	5	mV	
$\Delta V_O/\Delta I_{OUT}$	Load regulation	0 mA ≤ I <sub>OUT</sub> ≤ 200 mA			1		mV	
$V_{DO}$	Dropout voltage (1)	$V_{IN} = 0.98 \times V_{OUT(NOM)}, I_{C}$	<sub>OUT</sub> = 200 mA		145	250	mV	
I <sub>CL</sub>	Output current limit	$V_{OUT} = 0.9 \times V_{OUT(NOM)}$ , T	-J = +25°C	260	400	550	mA	
ı	Ground pin current	I <sub>OUT</sub> = 0 mA			35	55	μΑ	
I <sub>GND</sub>	Ground pin current	I <sub>OUT</sub> = 200 mA			315		μΑ	
I <sub>SHUTDOWN</sub>	Shutdown ground pin current	$V_{EN} \le 0.4 \text{ V}, 2 \text{ V} \le V_{IN} \le 4$		1	1.8	μΑ		
PSRR	Power-supply	V <sub>IN</sub> = 2.3 V, V <sub>OUT</sub> = 1.8 V,	$V_{IN} = 2.3 \text{ V}, V_{OUT} = 1.8 \text{ V}, I_{OUT} = 10 \text{ mA}, f = 10 \text{ kHz}$		80		dB	
PSKK	rejection ratio	$V_{IN} = 2.3 \text{ V}, V_{OUT} = 1.8 \text{ V},$	$I_{OUT} = 10 \text{ mA}, f = 1 \text{ MHz}$		55		dB	
	Output noise voltage	5144	V <sub>IN</sub> = 2.3 V, V <sub>OUT</sub> = 1.8 V		26.6		$\mu V_{RMS}$	
		BW = 100 Hz to 100 kHz, I <sub>OUT</sub> = 10 mA	$V_{IN} = 3.3 \text{ V}, V_{OUT} = 2.8 \text{ V}$		26.7		$\mu V_{\text{RMS}}$	
V			$V_{IN} = 3.8 \text{ V}, V_{OUT} = 3.3 \text{ V}$		28.2		$\mu V_{\text{RMS}}$	
$V_N$			$V_{IN} = 2.3 \text{ V}, V_{OUT} = 1.8 \text{ V}$		30.7		$\mu V_{\text{RMS}}$	
			$BW = 10 Hz \text{ to } 100 \text{ kHz},$ $I_{OUT} = 10 \text{ mA}$	$V_{IN} = 3.3 \text{ V}, V_{OUT} = 2.8 \text{ V}$		31.3		$\mu V_{RMS}$
		1001 = 10 11111	$V_{IN} = 3.8 \text{ V}, V_{OUT} = 3.3 \text{ V}$		34.1		$\mu V_{RMS}$	
t <sub>STR</sub>	Startup time (2)	$C_{OUT} = 1 \mu F$ , $I_{OUT} = 200 \text{ m}$	nA		100		μs	
$V_{HI}$	Enable high (enabled)			0.9		$V_{\text{IN}}$	V	
$V_{LO}$	Enable low (disabled)			0		0.4	V	
I <sub>EN</sub>	EN pin current	EN = 5.5 V		0.01		μΑ		
UVLO	Undervoltage lockout	V <sub>IN</sub> rising		1.9		V		
t	Thermal shutdown	Shutdown, temperature increasing			+160		°C	
t <sub>SD</sub>	temperature	Reset, temperature decrea		+140		°C		
T <sub>J</sub>	Operating junction temperature			-40		+125	°C	

 $V_{DO}$  is measured for devices with  $V_{OUT(NOM)}$  = 2.35 V so that  $V_{IN}$  = 2.3 V. Startup time = time from EN assertion to 0.98 ×  $V_{OUT(NOM)}.$ 



### **FUNCTIONAL BLOCK DIAGRAMS**

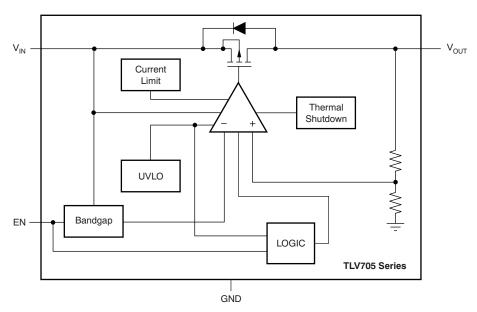


Figure 1. TLV705 Diagram

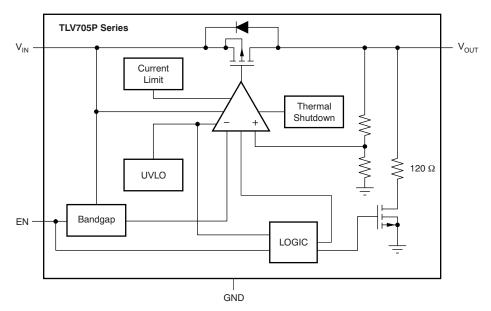


Figure 2. TLV705P Diagram



### **PIN CONFIGURATION**

YFF, YFP PACKAGES WCSP-4 (TOP VIEW)



**Table 1. Pin Descriptions** 

TLV705		
NAME	PIN#	DESCRIPTION
GND	A1	Ground pin
EN	A2	Enable pin. Driving EN over 0.9 V turns on the regulator. Driving EN below 0.4 V puts the regulator into shutdown mode, thus reducing operating current to 1 µA, nominal.
V <sub>OUT</sub>	B1	Regulated output voltage pin. A small 1-µF ceramic capacitor is required to be placed from this pin to ground to assure stability. See the <i>Input and Output Capacitor Requirements</i> section for more details.
V <sub>IN</sub>	B2	Input pin. A small 1-µF ceramic capacitor is recommended to be placed from this pin to ground for good transient performance. See the <i>Input and Output Capacitor Requirements</i> section for more details.



#### TYPICAL CHARACTERISTICS

Over operating temperature range ( $T_J = -40^{\circ}\text{C}$  to +125°C),  $I_{OUT} = 10$  mA,  $V_{EN} = 0.9$  V,  $C_{OUT} = 1$   $\mu\text{F}$ , and  $V_{IN} = V_{OUT(TYP)} + 0.5$  V or 2 V, whichever is greater, unless otherwise noted. Typical values are at  $T_J = +25^{\circ}\text{C}$ .

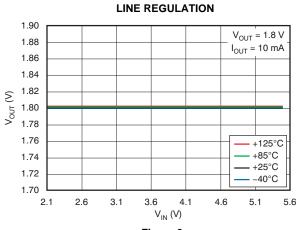


Figure 3.

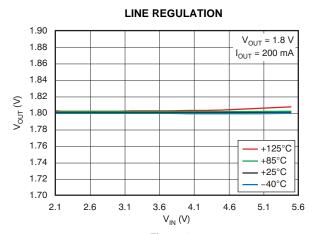
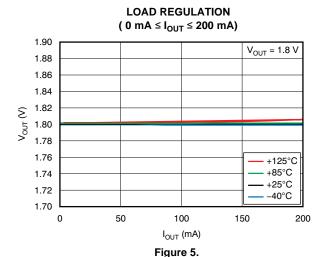
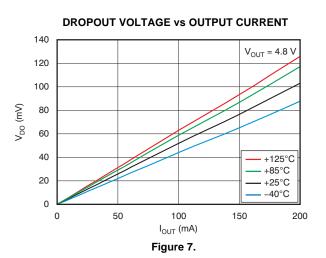
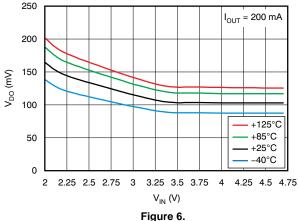


Figure 4.





DROPOUT VOLTAGE vs INPUT VOLTAGE



**OUTPUT VOLTAGE vs TEMPERATURE** 

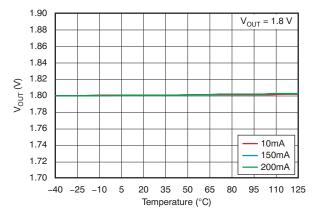
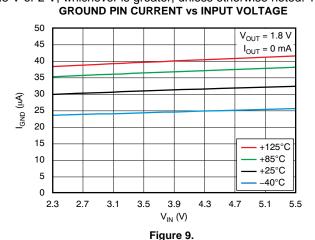


Figure 8.



Over operating temperature range ( $T_J = -40$ °C to +125°C),  $I_{OUT} = 10$  mA,  $V_{EN} = 0.9$  V,  $C_{OUT} = 1$   $\mu$ F, and  $V_{IN} = V_{OUT(TYP)} + 0.5$  V or 2 V, whichever is greater, unless otherwise noted. Typical values are at  $T_J = +25$ °C.



GROUND PIN CURRENT vs OUTPUT CURRENT

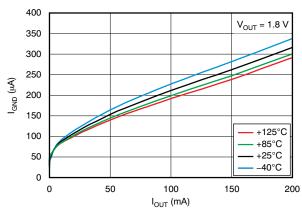
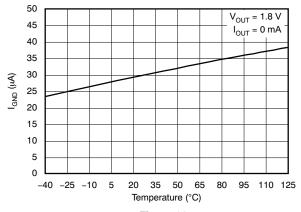


Figure 10.

#### **GROUND PIN CURRENT vs TEMPERATURE**



SHUTDOWN PIN CURRENT vs INPUT VOLTAGE

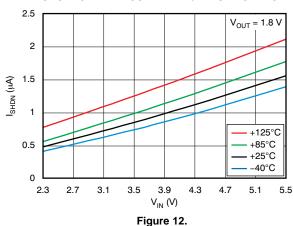
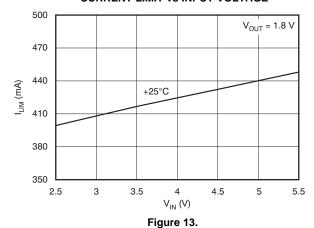


Figure 11.

### **CURRENT LIMIT vs INPUT VOLTAGE**



POWER-SUPPLY REJECTION RATIO vs FREQUENCY

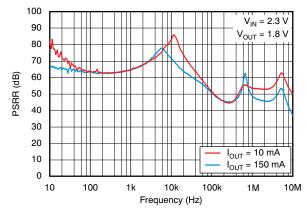


Figure 14.



Over operating temperature range (T<sub>J</sub> = -40 °C to +125 °C),  $I_{OUT}$  = 10 mA,  $V_{EN}$  = 0.9 V,  $C_{OUT}$  = 1  $\mu F$ , and  $V_{IN}$  =  $V_{OUT(TYP)}$  +

0.5 V or 2 V, whichever is greater, unless otherwise noted. Typical values are at  $T_J$  = +25°C.

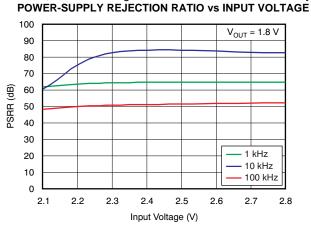


Figure 15.

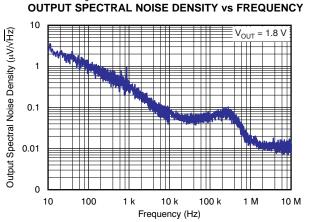


Figure 16.

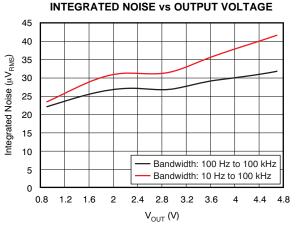


Figure 17.

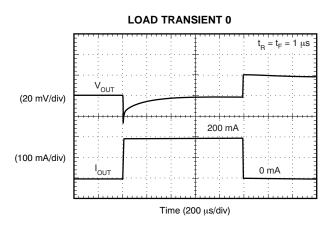


Figure 18.

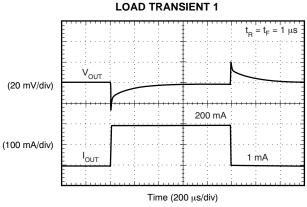


Figure 19.

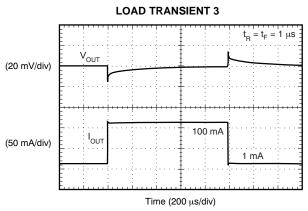


Figure 20.



Over operating temperature range ( $T_J = -40^{\circ}\text{C}$  to +125°C),  $I_{OUT} = 10$  mA,  $V_{EN} = 0.9$  V,  $C_{OUT} = 1$   $\mu\text{F}$ , and  $V_{IN} = V_{OUT(TYP)} + 0.5$  V or 2 V, whichever is greater, unless otherwise noted. Typical values are at  $T_J = +25^{\circ}\text{C}$ .

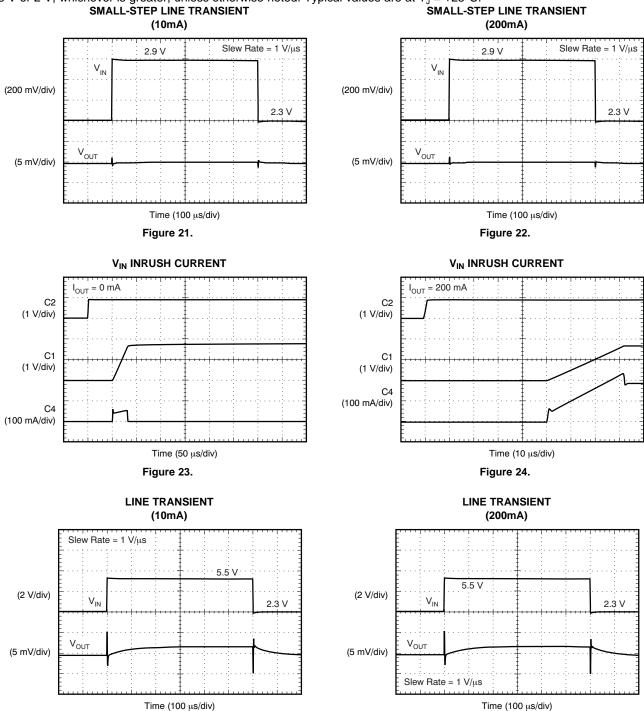


Figure 26.

Figure 25.



Over operating temperature range ( $T_J = -40^{\circ}\text{C}$  to +125°C),  $I_{OUT} = 10$  mA,  $V_{EN} = 0.9$  V,  $C_{OUT} = 1$   $\mu\text{F}$ , and  $V_{IN} = V_{OUT(TYP)} + 0.5$  V or 2 V, whichever is greater, unless otherwise noted. Typical values are at  $T_J = +25^{\circ}\text{C}$ . **POWER-UP/POWER-DOWN** 

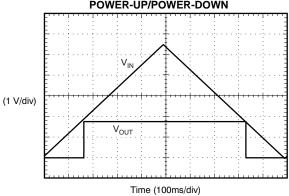


Figure 27.

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#### APPLICATION INFORMATION

The TLV705 and TLV705P series of devices belong to a new family of next-generation value low-dropout (LDO) voltage regulators. They consume low quiescent current and deliver excellent line and load transient performance. This performance, combined with low noise, very good PSRR with little ( $V_{\text{IN}} - V_{\text{OUT}}$ ) headroom, makes these devices ideal for RF portable applications. This family of regulators offers sub-bandgap output voltages down to 0.7 V, current limit, and thermal protection, and are specified from –40°C to +125°C. The TLV705P provides an active pull-down circuit to quickly discharge the outputs.

# INPUT AND OUTPUT CAPACITOR REQUIREMENTS

1-µF X5R- and X7R-type ceramic capacitors are recommended because these components have minimal variation in value and equivalent series resistance (ESR) over temperature. However, the TLV705 series is designed to be stable with an effective capacitance of 0.1 µF or larger at the output. Thus, the device would also be stable with capacitors of other dielectrics as long as the effective capacitance under the operating bias voltage and temperature is greater than 0.1 µF. This effective capacitance refers to the capacitance that the LDO sees under operating bias voltage and temperature conditions (that is, the capacitance after taking the voltage and temperature derating consideration). In addition to allowing the use of lower cost dielectrics, it also enables using smaller footprint capacitors that have higher derating space-constrained applications.

Note that using a 0.1- $\mu$ F rating capacitor at the output of the LDO does not ensure stability because the effective capacitance under operating conditions would be less than 0.1  $\mu$ F. Maximum ESR should be less than 200 m $\Omega$ .

Although an input capacitor is not required for stability, it is good analog design practice to connect a 0.1- $\mu F$  to 1- $\mu F$  low ESR capacitor across the  $V_{IN}$  and GND pins of the regulator. This capacitor counteracts reactive input sources and improves transient response, noise rejection, and ripple rejection. A higher-value capacitor may be necessary if large, fast rise-time load transients are anticipated, or if the device is not located close to the power source. If source impedance is more than 2  $\Omega,$  a 0.1- $\mu F$  input capacitor may be necessary to ensure stability.

# BOARD LAYOUT RECOMMENDATIONS TO IMPROVE PSRR AND NOISE PERFORMANCE

Input and output capacitors should be placed as close to the device pins as possible. To improve ac performance (such as PSRR, output noise, and transient response), it is recommended that the board be designed with separate ground planes for  $V_{\text{IN}}$  and  $V_{\text{OUT}},$  with the ground plane connected only at the GND pin of the device. In addition, the ground connection for the output capacitor should be connected directly to the GND pin of the device. High ESR capacitors may degrade PSRR.

#### INTERNAL CURRENT LIMIT

The internal current limits of the TLV705 series help protect the regulator during fault conditions. During current limit, the output sources a fixed amount of current that is largely independent of output voltage. In such a case, the output voltage is not regulated, and can be measured as  $V_{OUT} = I_{LIMIT} \times R_{LOAD}$ . The PMOS pass transistor dissipates  $[(V_{IN} - V_{OUT}) \times I_{LIMIT}]$  until a thermal shutdown is triggered and the device turns off. As the device cools down, it is turned on by the internal thermal shutdown circuit. If the fault condition continues, the device cycles between current limit and thermal shutdown; see the *Thermal Information* section for more details.

The PMOS pass element in the TLV705 has a built-in body diode that conducts current when the voltage at  $V_{\text{OUT}}$  exceeds the voltage at  $V_{\text{IN}}$ . This current is not limited, so if extended reverse voltage operation is anticipated, external limiting to 5% of rated output current is recommended.

#### **SOFT-START**

The startup current is given by Equation 1. This equation shows that soft-start current is directly proportional to  $C_{\text{OUT}}$ .

$$I_{SOFT-START} = C_{OUT} (\mu F) \times 0.06 (V/\mu s) + I_{LOAD} (mA)$$
 (1)

The output voltage ramp rate is independent of  $C_{\text{OUT}}$  and the load current, and has a typical value of 0.06 V/µs.

The TLV705 automatically adjusts the soft-start current to supply both the load current and the current to charge  $C_{OUT}.$  For example, if  $I_{LOAD}=0$  mA upon enabling the LDO, then  $I_{SOFT\text{-}START}=1$   $\mu\text{F}\times0.06$  V/ $\mu\text{s}+0$  mA = 60 mA, which is the current that charges the output capacitor. However if  $I_{LOAD}=200$  mA, then  $I_{SOFT\text{-}START}=1$   $\mu\text{F}\times0.06$  V/ $\mu\text{s}+200$  mA = 260 mA, which is the current required for charging the output capacitor and supplying the load current.



If the output capacitor and load are increased such that the soft-start current exceeds the output current limit, it is clamped at the typical current limit of 400 mA. For example, if  $C_{OUT}=10~\mu F$  and  $I_{OUT}=200$  mA, then 10  $\mu F$  × 0.06 V/ $\mu s$  + 200 mA = 800 mA is not supplied. Instead, it is clamped at 400 mA.

### **SHUTDOWN**

The enable pin (EN) is active high. The device is enabled when the EN pin goes above 0.9 V. This relatively lower value of voltage required to turn the LDO on can be used to power the device with the GPIO of recent processors with a GPIO voltage lower than traditional microcontrollers. The device is turned off when the EN pin is held at less than 0.4 V. When shutdown capability is not required, EN can be connected to the  $V_{\rm IN}$  pin. The TLV705P version has internal active pull-down circuitry that discharges the output with a time constant of:

$$T = (120 \times R_L)/(120 + R_L) \times C_{OUT}$$

Where:

$$R_L$$
 = load resistance,  $C_{OUT}$  = output capacitor (2)

#### **DROPOUT VOLTAGE**

The TLV705 uses a PMOS pass transistor to achieve low dropout. When  $(V_{\text{IN}}-V_{\text{OUT}})$  is less than the dropout voltage  $(V_{\text{DO}}),$  the PMOS pass device is in the linear region of operation and the input-to-output resistance is the  $R_{\text{DS}(\text{ON})}$  of the PMOS pass element.  $V_{\text{DO}}$  approximately scales with the output current because the PMOS device behaves as a resistor in dropout.

As with any linear regulator, PSRR and transient response are degraded as  $(V_{\text{IN}} - V_{\text{OUT}})$  approaches dropout. This effect is shown in Figure 15 in the Typical Characteristics.

#### TRANSIENT RESPONSE

As with any regulator, increasing the size of the output capacitor reduces over/undershoot magnitude, but increases the duration of the transient response.

### UNDERVOLTAGE LOCK-OUT (UVLO)

The TLV705 uses an undervoltage lockout (UVLO) circuit to keep the output shut off until the internal circuitry is operating properly.

#### THERMAL INFORMATION

Thermal protection disables the output when the junction temperature rises to approximately +165°C, allowing the device to cool. When the junction temperature cools to approximately +145°C, the output circuitry is again enabled. Depending on power

dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits the dissipation of the regulator, protecting it from damage as a result of overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heatsink. For reliable operation, junction temperature should be limited to +125°C, maximum. To estimate the margin of safety in a complete design heatsink), (including increase the ambient temperature until the thermal protection is triggered; use worst-case loads and signal conditions. For good reliability, thermal protection should trigger at least +35°C above the maximum expected ambient condition of the particular application. produces a worst-case configuration junction temperature of +125°C at the highest expected ambient temperature and worst-case load.

The internal protection circuitry of the TLV705 is been designed to protect against overload conditions. It is not intended to replace proper heatsinking. Continuously running the TLV705 into thermal shutdown degrades device reliability.

#### POWER DISSIPATION

The ability to remove heat from the die is different for each package type, presenting different considerations in the printed circuit board (PCB) layout. The PCB area around the device that is free of other components moves the heat from the device to the ambient air. Performance data for JEDEC low and high-K boards are given in the Thermal Information table. Using heavier copper increases the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers also improves the heatsink effectiveness.

Refer to Table 2 for thermal performance on the TLV705 evaluation module (EVM). The EVM is a two-layer board with two ounces of copper per side. Dimensions and layout of the board are illustrated in Figure 28 and Figure 29, respectively.

Power dissipation depends on input voltage and load conditions. Power dissipation ( $P_D$ ) is equal to the product of the output current and the voltage drop across the output pass element, as shown in Equation 3:

$$P_{D} = (V_{IN} - V_{OUT}) \times I_{OUT}$$
(3)



## Table 2. Power Dissipation Ratings<sup>(1)</sup>

BOA	RD PACKAGE	$R_{ hetaJ}$	T <sub>A</sub> ≤ 25°C POWER RATING	T <sub>A</sub> = +70°C POWER RATING	T <sub>A</sub> = +85°C POWER RATING
High	-K YFF, YFP	140 °C/W	714 mW	392 mW	285 mW

(1) Thermal resistance as measured on the evaluation module (EVM).

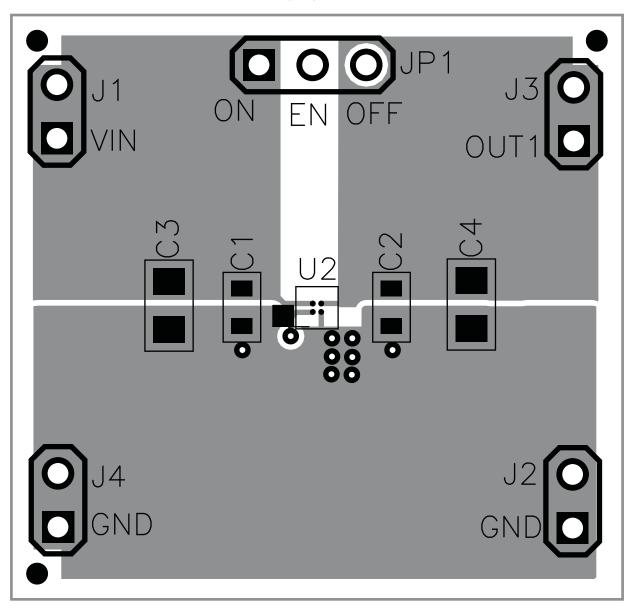


Figure 28. Silkscreen, Top Layer



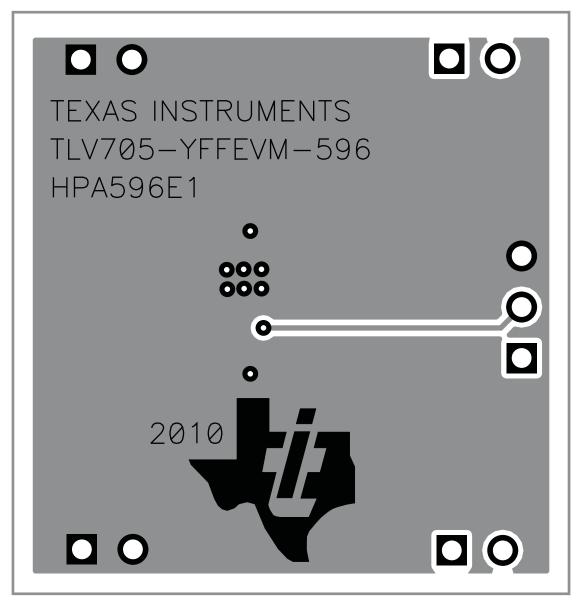
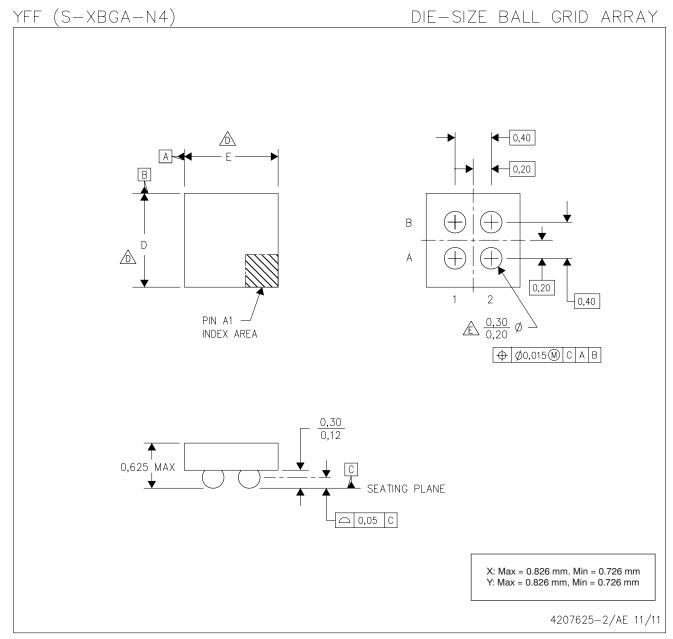


Figure 29. Silkscreen, Bottom Layer



### **MECHANICAL PACKAGES**

Figure 30 and Figure 31 show the YFF and YFP mechanical packages, respectively, with maximum and minimum heights noted.



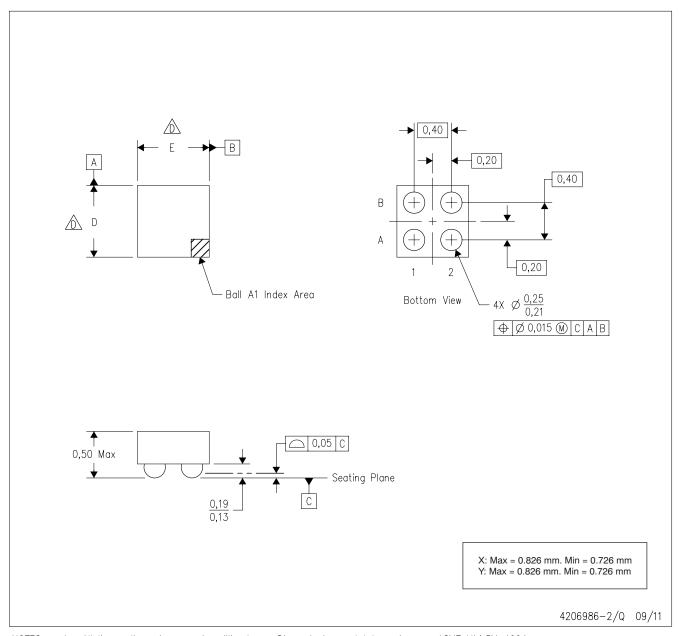
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  - B. This drawing is subject to change without notice.
  - Ç. NanoFree™ package configuration.
  - The package size (Dimension D and E) of a particular device is specified in the device Product Data Sheet version of this drawing, in case it cannot be found in the product data sheet please contact a local TI representative.
  - E. Reference Product Data Sheet for array population. 2 x 2 matrix pattern is shown for illustration only.
  - F. This package contains Pb-free balls.

Figure 30. YFF Package



# YFP (S-XBGA-N4)

### DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

The package size (Dimension D and E) of a particular device is specified in the device Product Data Sheet version of this drawing, in case it cannot be found in the product data sheet please contact a local TI representative.

- E. Reference Product Data Sheet for array population. 2 x 2 matrix pattern is shown for illustration only.
- F. This package contains Pb-free balls.

Figure 31. YFP Package





### **REVISION HISTORY**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	hanges from Revision A (August 2011) to Revision B	Page
•	Added last Features bullet	1
•	Changed front page pin out drawing	
•	Changed last sentence of Description section	1
•	Added YFP package to Thermal Information table	2
•	Added YFP to title of pin out drawing	5
•	Added YFP to Package column of Table 2	13
•	Added Mechanical Packages section	15

25-Jun-2012

### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
TLV705185YFPR	ACTIVE	DSBGA	YFP	4	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV705185YFPT	ACTIVE	DSBGA	YFP	4	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70518YFPR	ACTIVE	DSBGA	YFP	4	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70518YFPT	ACTIVE	DSBGA	YFP	4	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70525YFPR	ACTIVE	DSBGA	YFP	4	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70525YFPT	ACTIVE	DSBGA	YFP	4	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70528YFPR	ACTIVE	DSBGA	YFP	4	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70528YFPT	ACTIVE	DSBGA	YFP	4	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70530YFPR	ACTIVE	DSBGA	YFP	4	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70530YFPT	ACTIVE	DSBGA	YFP	4	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70533YFFR	ACTIVE	DSBGA	YFF	4	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70533YFFT	ACTIVE	DSBGA	YFF	4	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70533YFPR	ACTIVE	DSBGA	YFP	4	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TLV70533YFPT	ACTIVE	DSBGA	YFP	4	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.



### PACKAGE OPTION ADDENDUM

25-Jun-2012

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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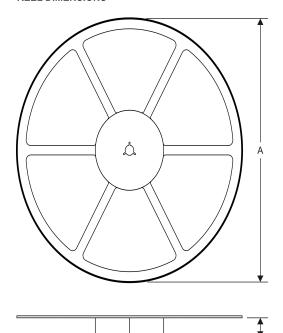
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# PACKAGE MATERIALS INFORMATION

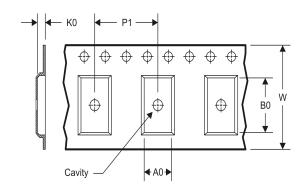
www.ti.com 23-Jun-2012

### TAPE AND REEL INFORMATION

### **REEL DIMENSIONS**



### **TAPE DIMENSIONS**



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### TAPE AND REEL INFORMATION

\*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV705185YFPR	DSBGA	YFP	4	3000	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV705185YFPT	DSBGA	YFP	4	250	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70518YFPR	DSBGA	YFP	4	3000	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70518YFPT	DSBGA	YFP	4	250	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70525YFPR	DSBGA	YFP	4	3000	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70525YFPT	DSBGA	YFP	4	250	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70528YFPR	DSBGA	YFP	4	3000	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70528YFPT	DSBGA	YFP	4	250	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70530YFPR	DSBGA	YFP	4	3000	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70530YFPT	DSBGA	YFP	4	250	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70533YFFR	DSBGA	YFF	4	3000	180.0	8.4	0.85	0.85	0.64	4.0	8.0	Q1
TLV70533YFFT	DSBGA	YFF	4	250	180.0	8.4	0.85	0.85	0.64	4.0	8.0	Q1
TLV70533YFPR	DSBGA	YFP	4	3000	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1
TLV70533YFPT	DSBGA	YFP	4	250	180.0	8.4	0.86	0.86	0.59	4.0	8.0	Q1

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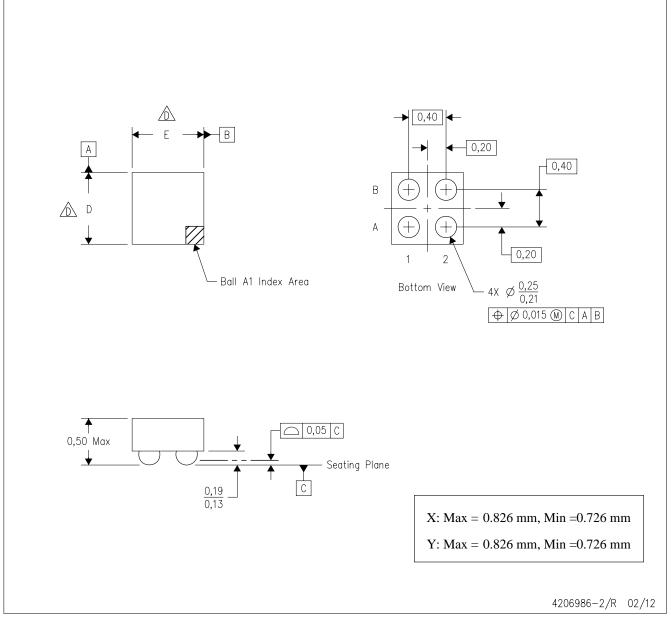


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV705185YFPR	DSBGA	YFP	4	3000	210.0	185.0	35.0
TLV705185YFPT	DSBGA	YFP	4	250	210.0	185.0	35.0
TLV70518YFPR	DSBGA	YFP	4	3000	210.0	185.0	35.0
TLV70518YFPT	DSBGA	YFP	4	250	210.0	185.0	35.0
TLV70525YFPR	DSBGA	YFP	4	3000	210.0	185.0	35.0
TLV70525YFPT	DSBGA	YFP	4	250	210.0	185.0	35.0
TLV70528YFPR	DSBGA	YFP	4	3000	210.0	185.0	35.0
TLV70528YFPT	DSBGA	YFP	4	250	210.0	185.0	35.0
TLV70530YFPR	DSBGA	YFP	4	3000	210.0	185.0	35.0
TLV70530YFPT	DSBGA	YFP	4	250	210.0	185.0	35.0
TLV70533YFFR	DSBGA	YFF	4	3000	210.0	185.0	35.0
TLV70533YFFT	DSBGA	YFF	4	250	210.0	185.0	35.0
TLV70533YFPR	DSBGA	YFP	4	3000	210.0	185.0	35.0
TLV70533YFPT	DSBGA	YFP	4	250	210.0	185.0	35.0

# YFP (S-XBGA-N4)

### DIE-SIZE BALL GRID ARRAY



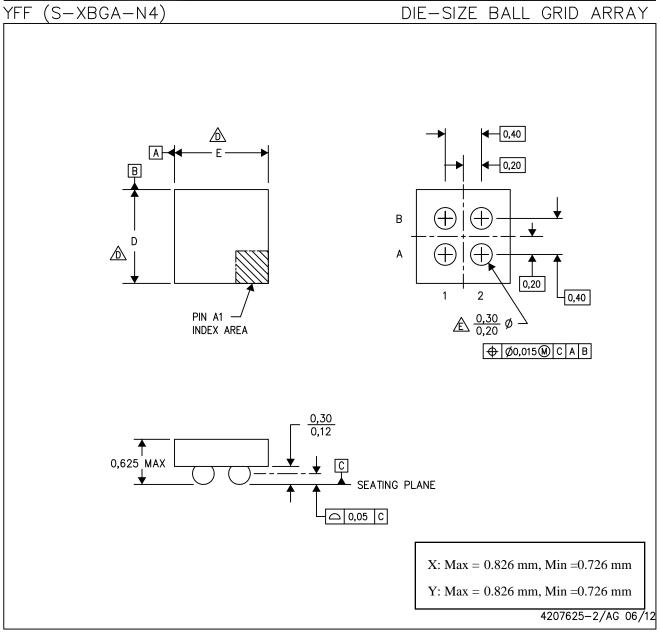
NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

The package size (Dimension D and E) of a particular device is specified in the device Product Data Sheet version of this drawing, in case it cannot be found in the product data sheet please contact a local TI representative.

- E. Reference Product Data Sheet for array population. 2 x 2 matrix pattern is shown for illustration only.
- F. This package contains Pb-free balls.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- Ç. NanoFree™ package configuration.

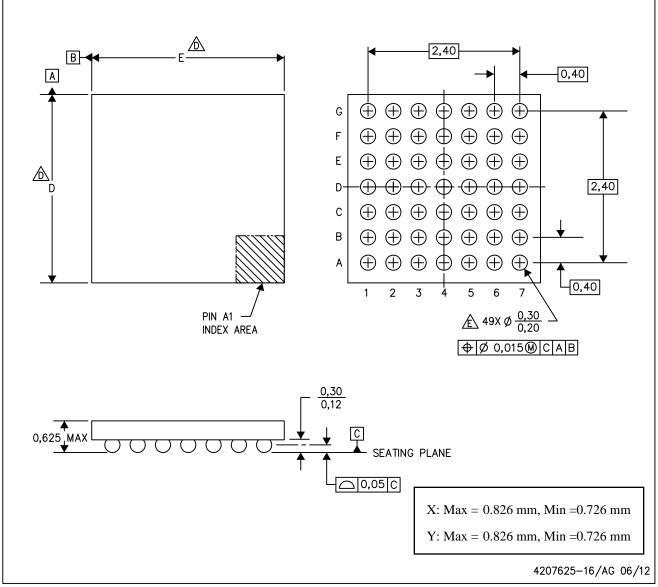
The package size (Dimension D and E) of a particular device is specified in the device Product Data Sheet version of this drawing, in case it cannot be found in the product data sheet please contact a local TI representative.

- E. Reference Product Data Sheet for array population. 2 x 2 matrix pattern is shown for illustration only.
- F. This package contains Pb—free balls.



## YFF (R-XBGA-N49)

### DIE-SIZE BALL GRID ARRAY

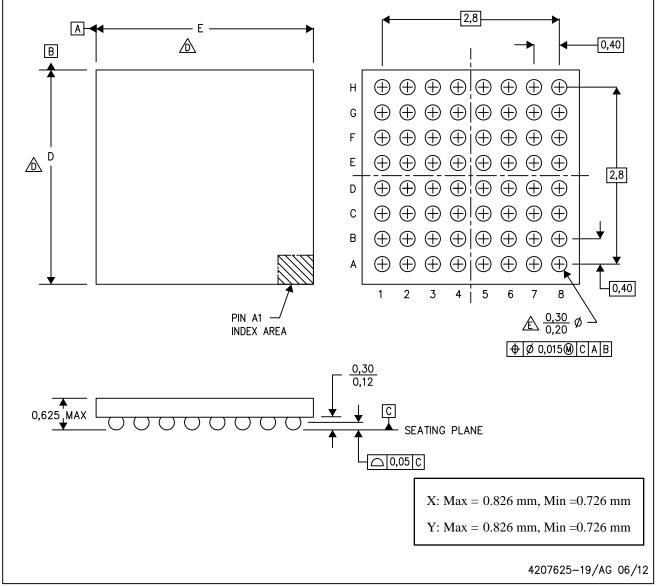


- NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. NanoFree™ package configuration.
  - The package size (Dimension D and E) of a particular device is specified in the device Product Data Sheet version of this drawing, in case it cannot be found in the product data sheet please contact a local TI representative.
  - E. Reference Product Data Sheet for array population.7 x 7 matrix pattern is shown for illustration only.
  - F. This package contains Pb-free balls.



## YFF (R-XBGA-N64)

### DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

The package size (Dimension D and E) of a particular device is specified in the device Product Data Sheet version of this drawing, in case it cannot be found in the product data sheet please contact a local TI representative.

- E Reference Product Data Sheet for array population. 8 x 8 matrix pattern is shown for illustration only.
- F. This package contains Pb-free balls.



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